

0.05 μ V/ $^{\circ}$ C max, Zero-Drift, Single Supply, Rail-to-Rail Output CMOS Operational Amplifier

FEATURES ($V^+ = 5V$, Typical value)

• Low Offset Voltage	15 μ V max.
• Zero-Drift	0.05 μ V/ $^{\circ}$ C max.
• Supply Voltage Range	3V to 10V
• Rail-to-Rail Output ($R_L = 10k\Omega$)	20mV from rail
• Output Current ($V_O = 4.5V$ at $V^+ = 5V$)	30mA
• DC Precision	
Open-Loop Voltage Gain	140dB
CMR, SVR	130dB
• Supply Current	0.6mA
• Shutdown	
• RF-Noise immunity	
• Ground Sense	
• Overload Recovery Time	0.45ms
• Package	SOT-23-6-1

APPLICATIONS

- Thermocouple Amplifiers
- Electronic Scales
- Strain Gauge Amplifiers
- Medical Instrumentation
- Precision Current Sensing
- High Resolution Data Acquisition
- Low-Side Current Sensing
- Handheld Test Equipment

DESCRIPTION

The NJU7098AF1-C is a low offset voltage and zero-drift operational amplifier. With an maximum input offset voltage of 15 μ V and offset drift of 0.05 μ V/ $^{\circ}$ C, the NJU7098AF1-C is suitable for applications in which error sources cannot be tolerated.

The NJU7098AF1-C operate from 3V to 10V with single supply. Rail-to-rail output swing , input common mode voltage within negative rail and 30mA high output current capability provided by the NJU7098AF1-C make low-side sensing or precision output buffer easy.

The almost zero DC offset and offset drift are supported with a power supply rejection ratio and common mode rejection ratio at 130dB. Futuremore, typical open-loop voltage gain is 140dB.

The NJU7098AF1-C includes a shutdown mode. Under logic control, the amplifiers can be switched from normal operation to shutdown current that is 15 μ A max and the output placed in a high- impedance state.

■ PIN CONFIGURATIONS

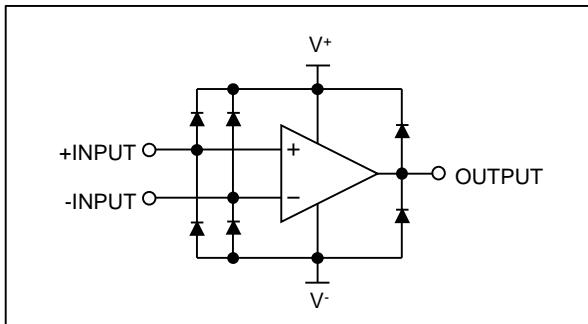
PRODUCT NAME	NJU7098AF1-C				
Package	SOT-23-6-1				
Pin Functions					

■ PRODUCT NAME INFORMATION

NJU7098A F1 - C (TE1)
 Part Number Package Sorting Index Taping Form

■ ORDERING INFORMATION

PRODUCT NAME	PACKAGE	RoHS	HALOGEN-FREE	TERMINAL FINISH	MARKING	WEIGHT (mg)	MOQ (pcs)
NJU7098AF1-C	SOT-23-6-1			Sn2Bi	E4	15	3000

■ BLOCK DIAGRAM

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	$V^+ - V^-$	11	V
Input Voltage ⁽¹⁾	V_{IN}	$V - 0.3$ to $V^+ + 0.3$	V
Differential Input Voltage ⁽³⁾	V_{ID}	$\pm 11^{(2)}$	V
Power Dissipation ($T_a = 25^\circ C$) SOT-23-6-1	P_D	2-Layer / 4-Layer ⁽³⁾ 410 / 580	mW
Storage Temperature Range	T_{stg}	-40 to 125	°C
Maximum Junction Temperature	T_{jmax}	125	°C

■ THERMAL CHARACTERISTICS

PACKAGE	SYMBOL	VALUE	UNIT
Junction-to-Ambient Thermal Resistance SOT-23-6-1	Θ_{ja}	2-Layer / 4-Layer ⁽³⁾ 244 / 172	°C/W
Junction-to-Top of Package Characterization Parameter SOT-23-6-1	Ψ_{jt}	2-Layer / 4-Layer ⁽³⁾ 70 / 59	°C/W

(1) Differential voltage is the voltage difference between +INPUT and -INPUT.

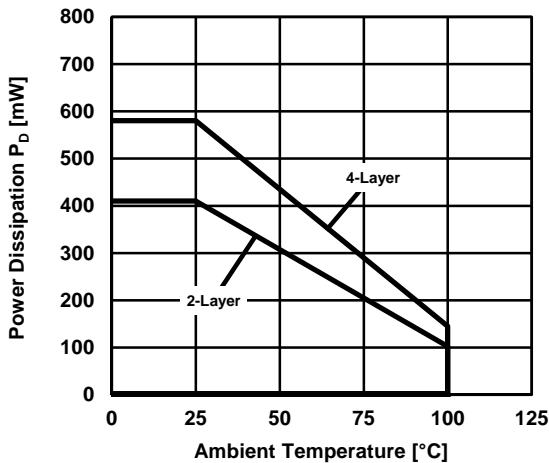
(2) For supply voltage less than 15V, the absolute maximum rating is equal to the supply voltage.

(3) 2-layer: Mounted on glass epoxy board. (76.2x114.3x1.6mm: based on EIA/JDEC standard, 2-layer FR-4)

4-layer: Mounted on glass epoxy board. (76.2x114.3x1.6mm: based on EIA/JDEC standard, 4-layer FR-4), internal Cu area: 74.2x74.2mm

■ POWER DISSIPATION vs. AMBIENT TEMPERATURE

Power Dissipation vs. Temperature



■ RECOMMENDED OPERATING CONDITIONS

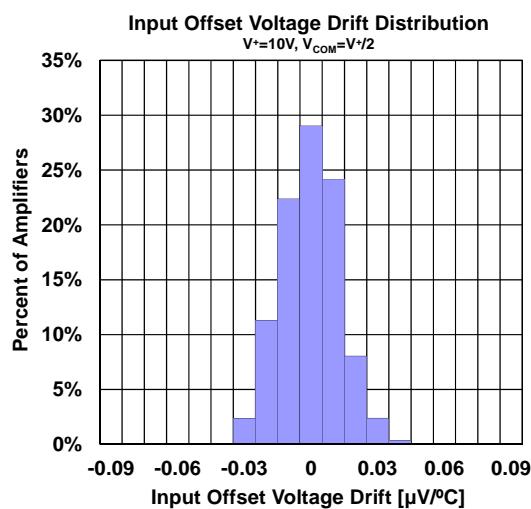
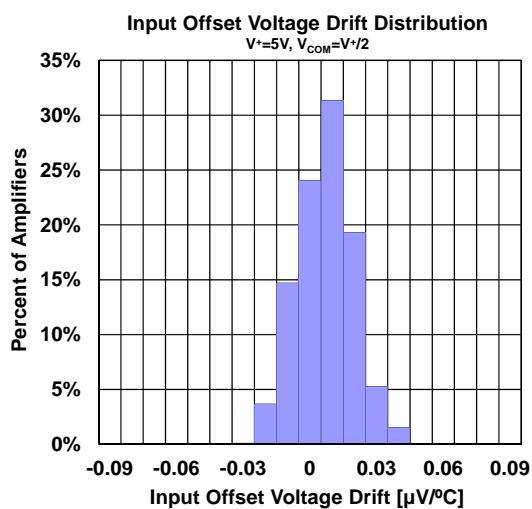
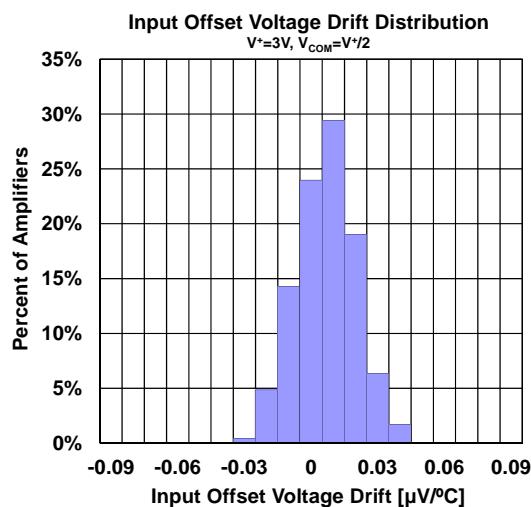
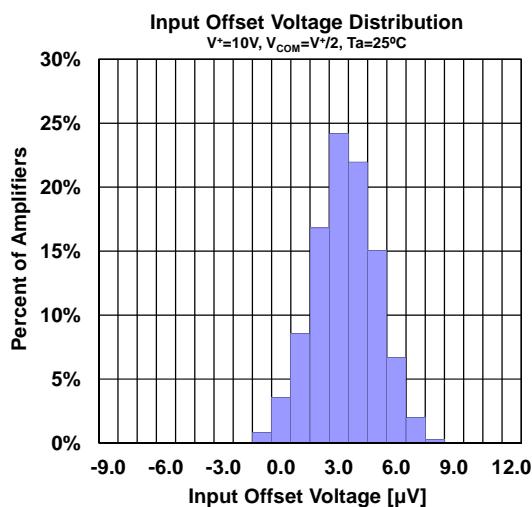
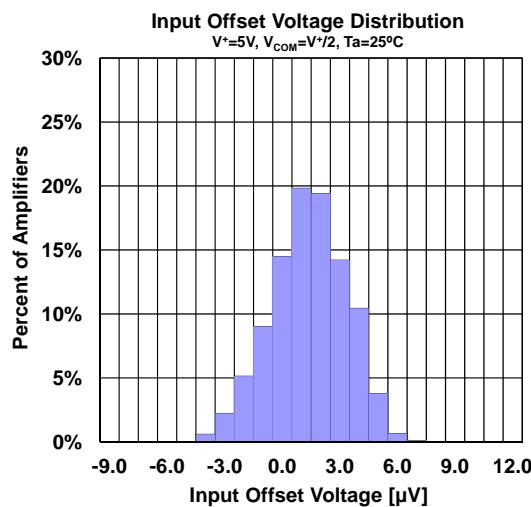
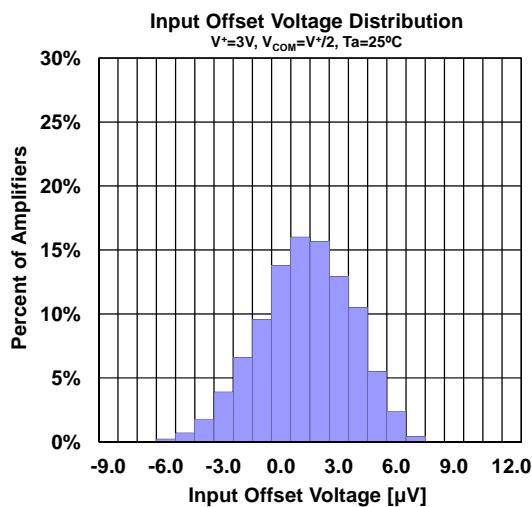
PARAMETER	SYMBOL	CONDITIONS	VALUE	UNIT
Supply Voltage	$V^+ - V^-$	$T_a = 25^\circ C$	3 to 10	V
Operating Temperature Range	T_{opr}		-40 to 105	°C

■ ELECTRICAL CHARACTERISTICS ($V^+=5V$, $V=0V$, $V_{SHDN}=V^+$, $T_a=25^\circ C$, unless otherwise noted.)

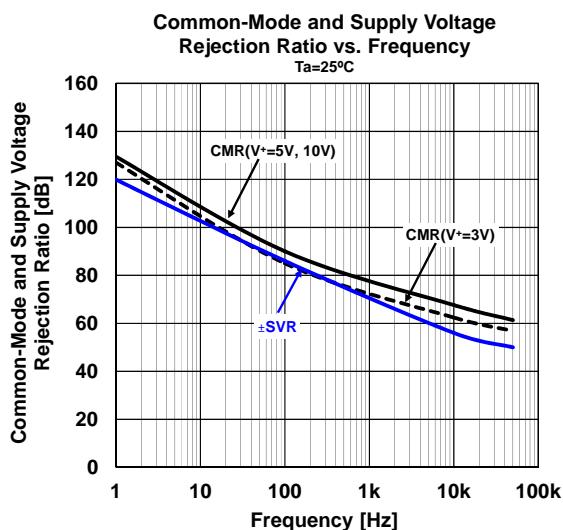
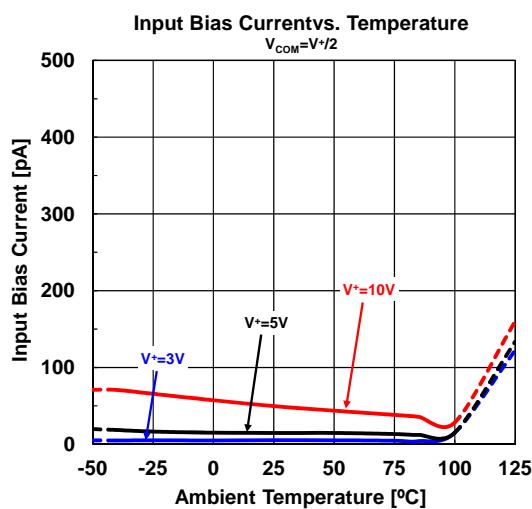
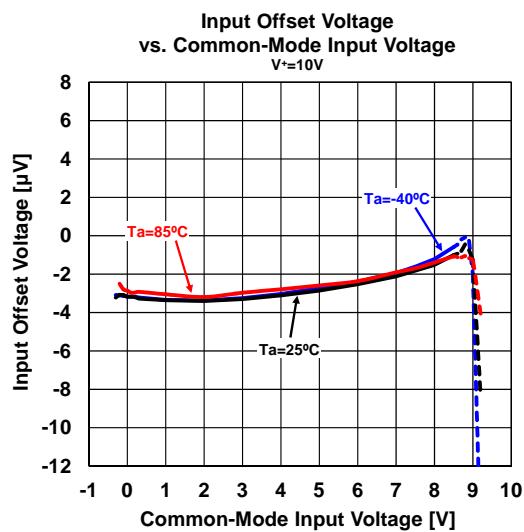
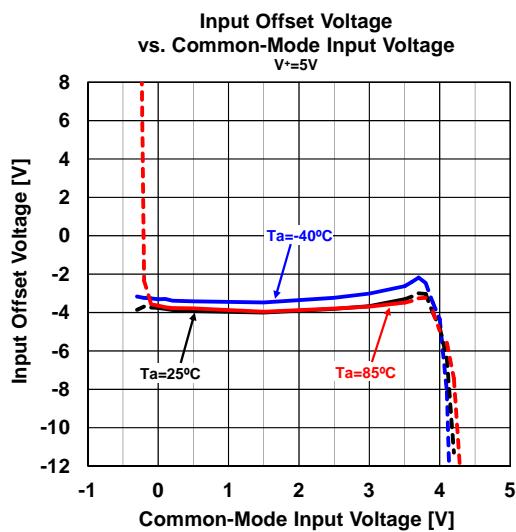
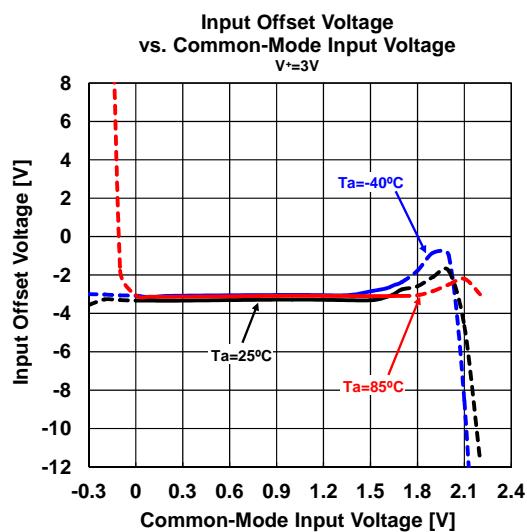
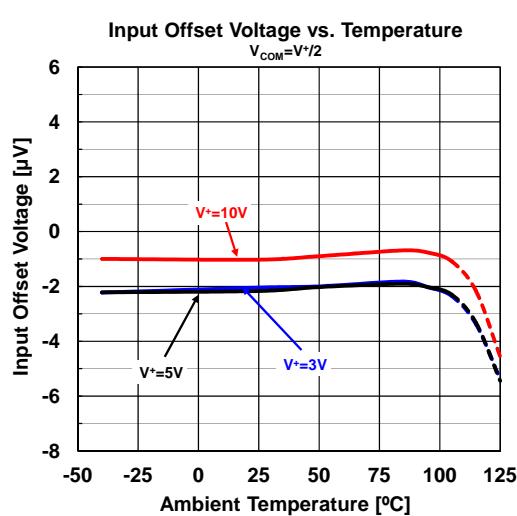
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC CHARACTERISTICS						
Input Offset Voltage	V_{IO}	$T_a=-40^\circ C$ to $85^\circ C$, $V^+=3V$ to $10V$	-	3	15	μV
Input Offset Voltage Drift ⁽⁴⁾	$V_{IO}/\Delta T$	$T_a=-40^\circ C$ to $85^\circ C$, $V^+=3V$ to $10V$	-	-	0.05	$\mu V/^\circ C$
Input Bias Current	I_B		-	20	400	pA
Input Offset Current	I_O		-	-	500	pA
Open-Loop Voltage Gain	A_V	$R_L \geq 10k\Omega$, $V_O=1$ to $4V$	120	140	-	dB
Common-Mode Input Voltage Range	V_{ICM}	CMR $\geq 100dB$	0	-	3.5	V
Common-Mode Rejection Ratio	CMR	$V_{ICM}=0$ to $3.5V$	100	130	-	dB
Supply Voltage Rejection Ratio	SVR	$V^+=4$ to $10V$	100	130	-	dB
High-level Output Voltage	V_{OH}	$R_L=10k\Omega$ to $0V$ $R_L=2k\Omega$ to $0V$	4.95 4.85	4.98 4.94	-	V
Low-level Output Voltage	V_{OL}	$R_L=10k\Omega$ to $0V$ $R_L=2k\Omega$ to $0V$	- -	1 1	10 10	mV
Output Source Current	I_{SOURCE}	$V_O=4.5V$	10	30	-	mA
Output Sink Current	I_{SINK}	$V_O=0.5V$	4	40	-	mA
Supply Current		No Signal				
Normally Mode	I_{SUPPLY}	$V_{SHDN}=5V$	-	0.6	1.2	mA
Shutdown Mode		$V_{SHDN}=0V$	-	-	15	μA
Shutdown Pin Input High Voltage	V_{SHDNON}	$I_{SUPPLY} \geq 300\mu A$	4.5	-	5	V
Shutdown Pin Input Low Voltage	$V_{SHDNOFF}$	$I_{SUPPLY} \leq 10\mu A$	0	-	0.5	V
Shutdown Pin Input Current	I_{SHDN}	$V_{SHDN}=0V$	-	2	7	μA
AC CHARACTERISTICS						
Gain Bandwidth Product	GBW	$R_L=10k\Omega$	-	3	-	MHz
Positive Slew Rate	+SR	$G_V=+1$, $R_L=10k\Omega$	-	3	-	$V/\mu s$
Negative Slew Rate	-SR	$G_V=-1$, $R_L=10k\Omega$	-	12	-	$V/\mu s$
Phase Margin	Φ_M	$R_L=10k\Omega$, $C_L=50pF$	-	30	-	deg
Equivalent Input Noise Voltage	V_{NI}	$f=10Hz$	-	120	-	nV/\sqrt{Hz}
Internal Sampling Frequency	F_S		-	7.5	-	kHz

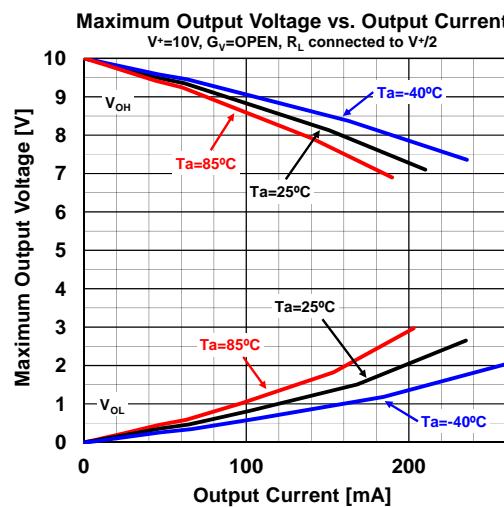
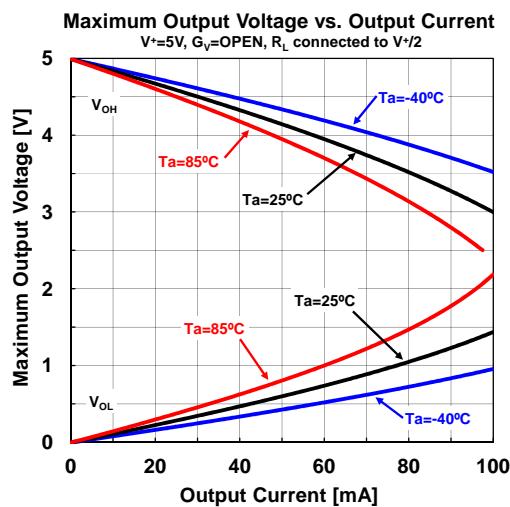
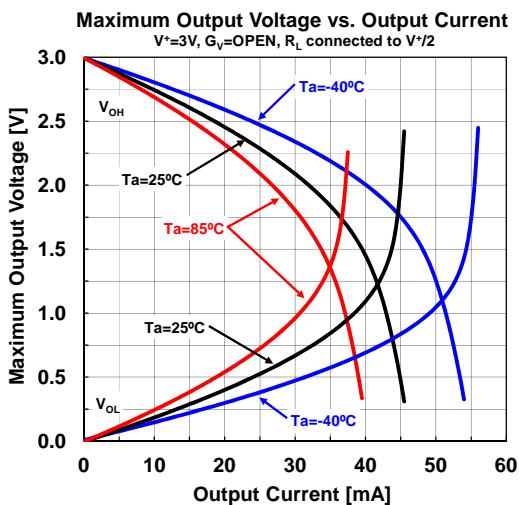
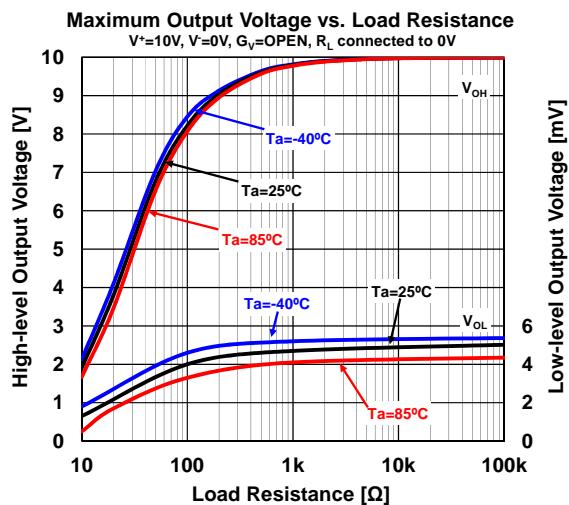
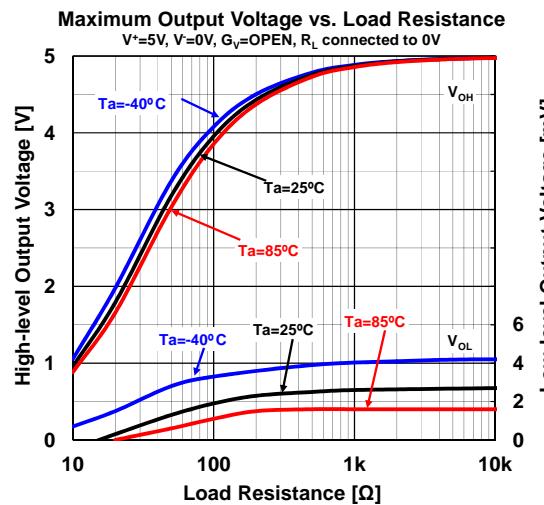
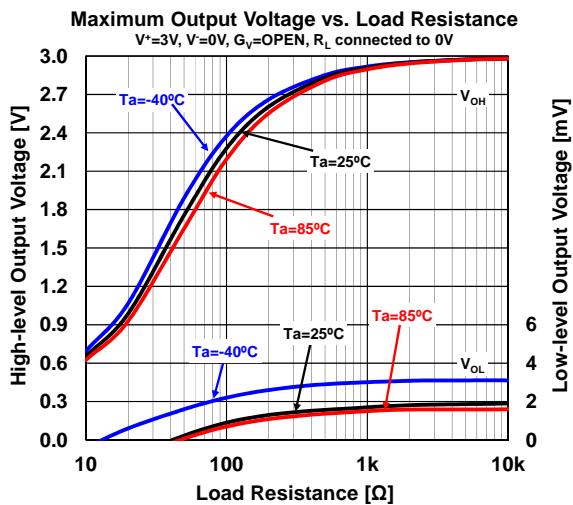
(4) Guaranteed by design.

■ TYPICAL CHARACTERISTICS

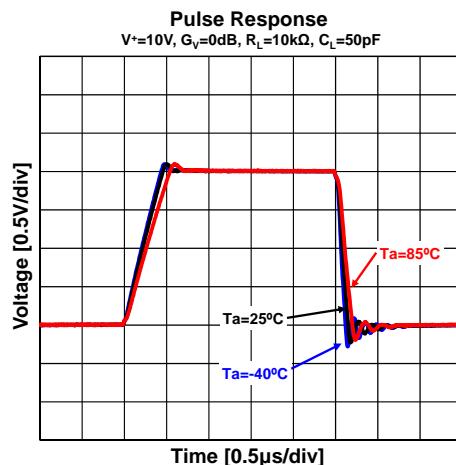
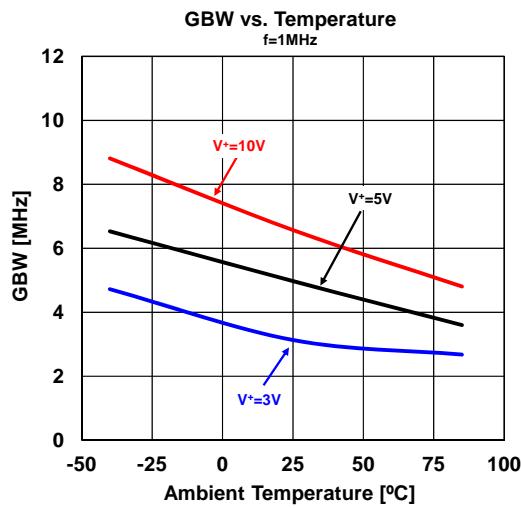
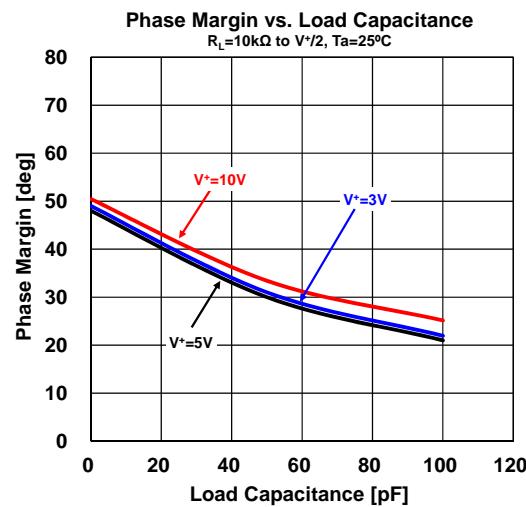
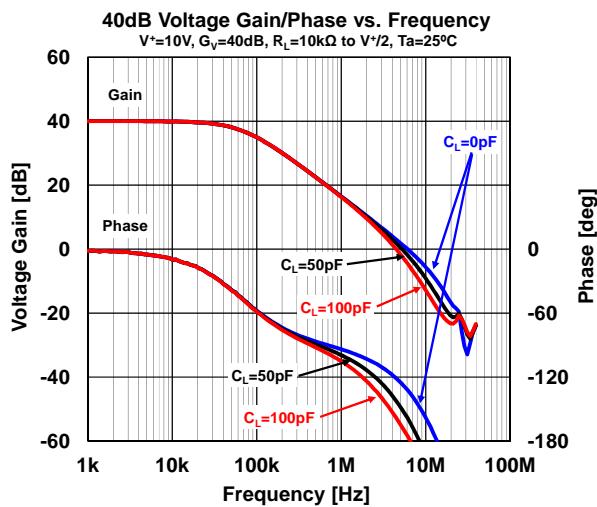
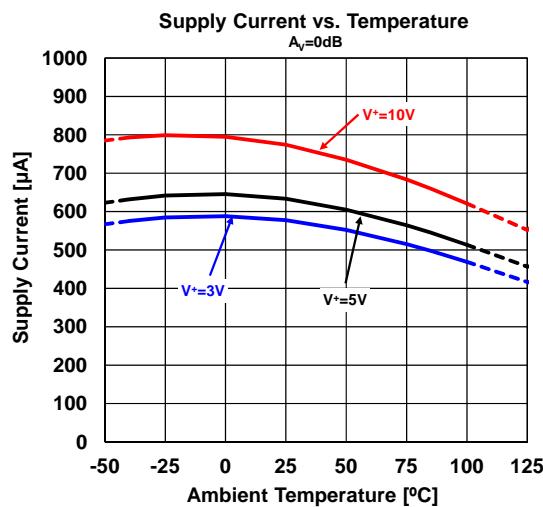
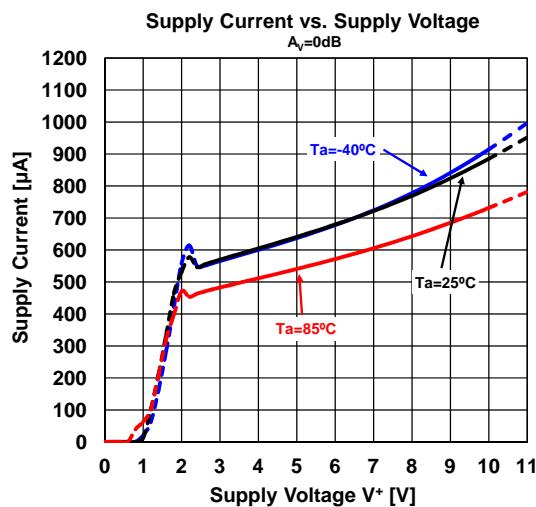


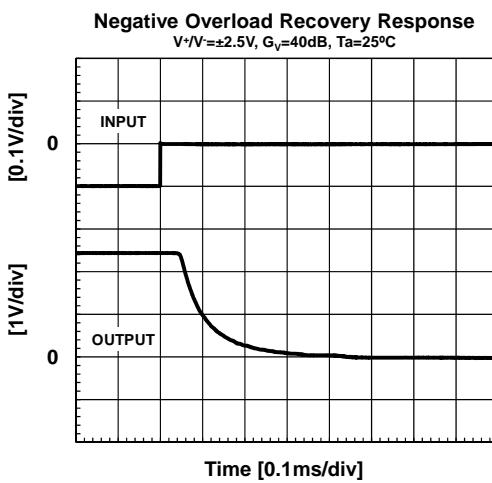
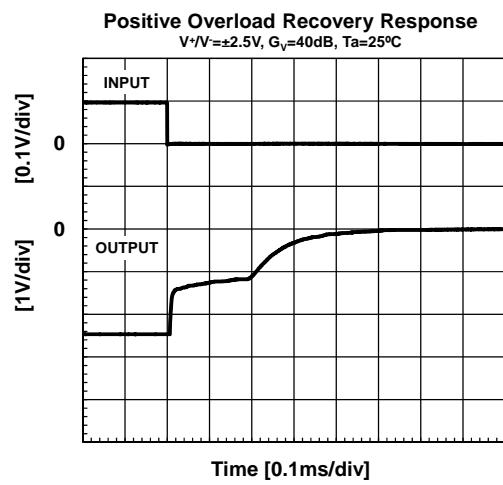
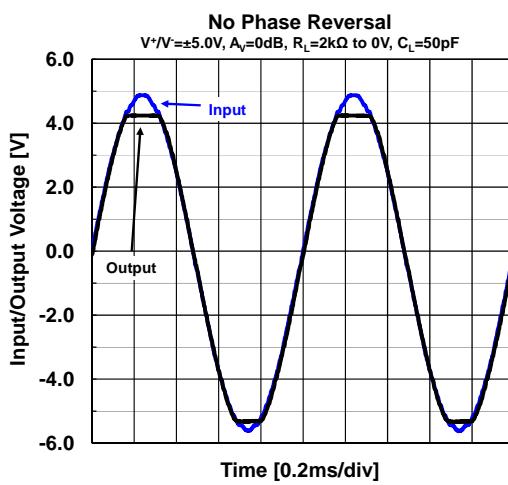
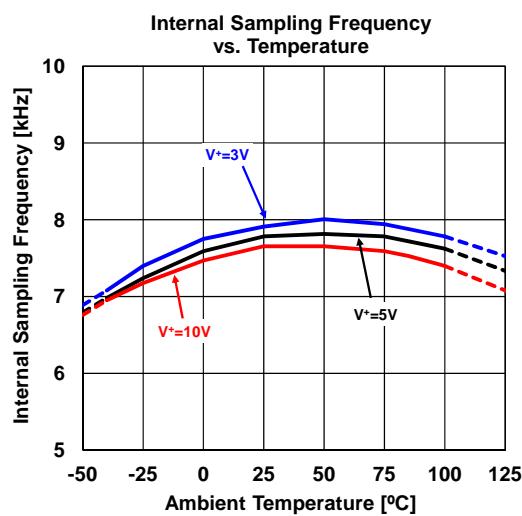
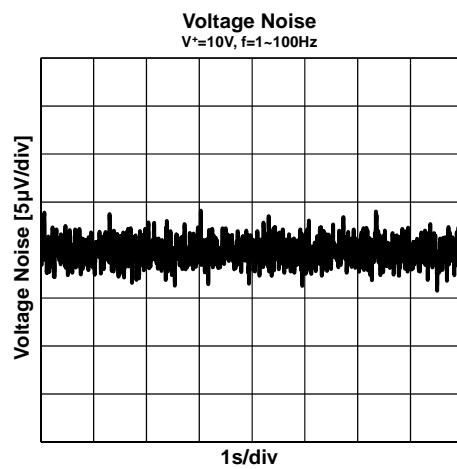
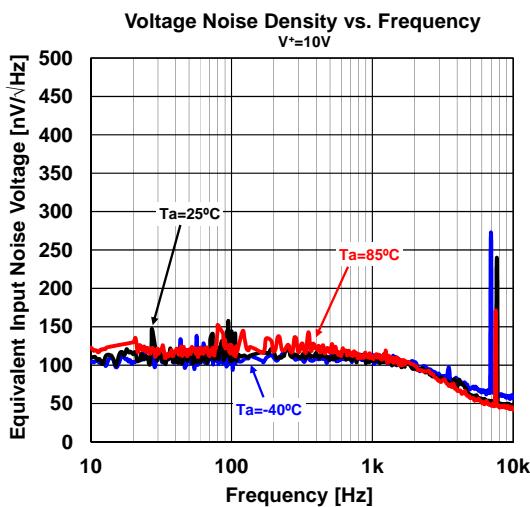
■ TYPICAL CHARACTERISTICS



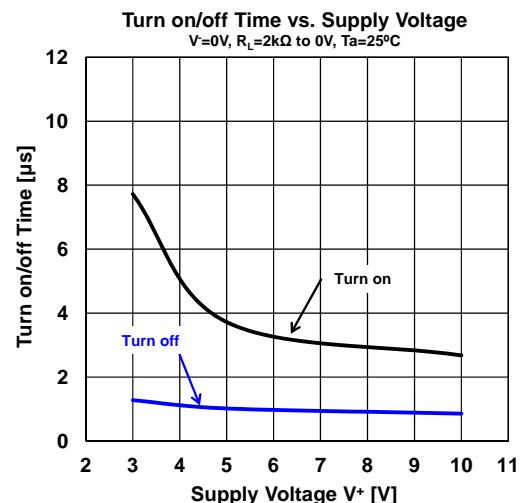
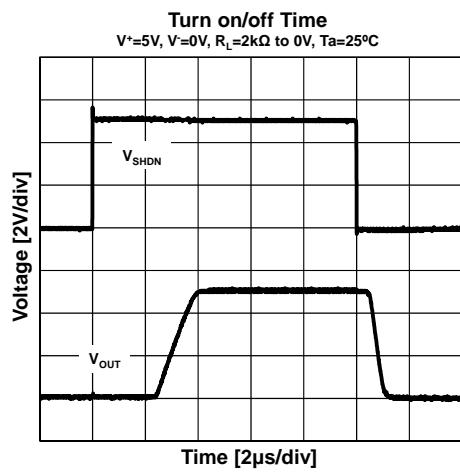
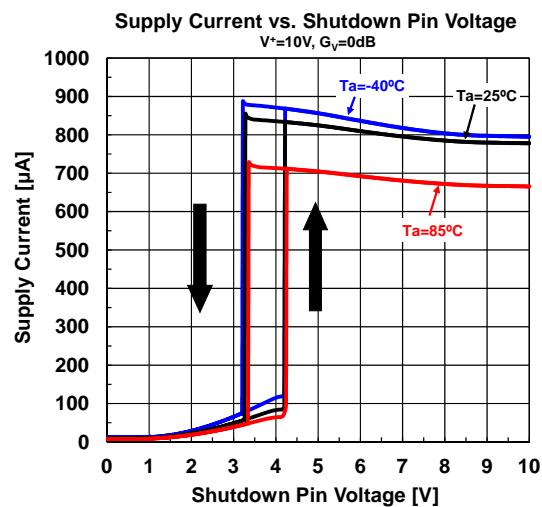
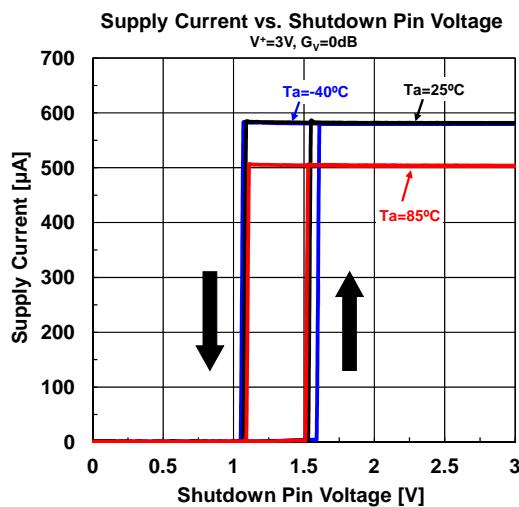
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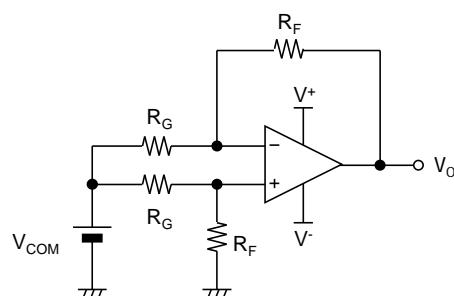
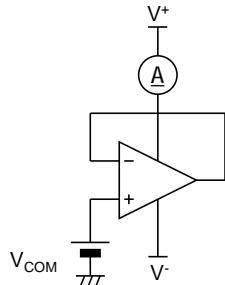


■ TEST CIRCUITS

- I_{SUPPLY}

 $V_{COM}=V^+/2$

- V_{IO} , CMR, SVR

 $R_G=10\Omega, R_F=100k\Omega, V_{COM}=V^+/2$


$$V_{IO} = \frac{R_F}{(R_G + R_F)} \times (V_0 - V_{COM})$$

$$CMR = 20 \log \frac{\Delta V_{COM} \left(1 + \frac{R_F}{R_G} \right)}{\Delta V_O}$$

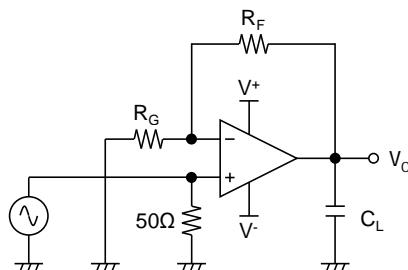
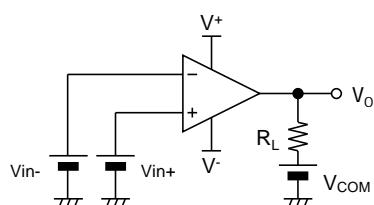
$$SVR = 20 \log \frac{\Delta V_S \left(1 + \frac{R_F}{R_G} \right)}{\Delta V_O}$$

$$V_S = V^+ - V^-$$

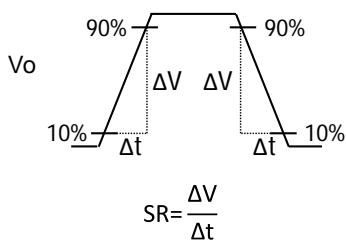
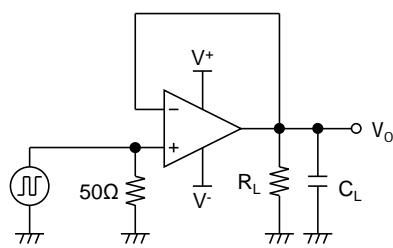
- V_{OH}, V_{OL}

 $V_{OH}; V_{in+} = 1V, V_{in-} = 0V, V_{COM}=0V$
 $V_{OL}; V_{in+} = 0V, V_{in-} = 1V, V_{COM}=0V$

- GBW

 $R_G=100\Omega, R_F=10k\Omega$


- SR

 $R_L=10k\Omega$


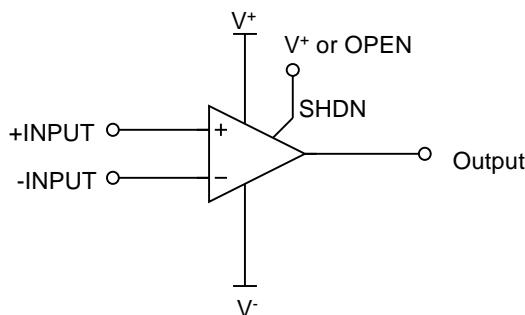
■ Application Note

Shutdown

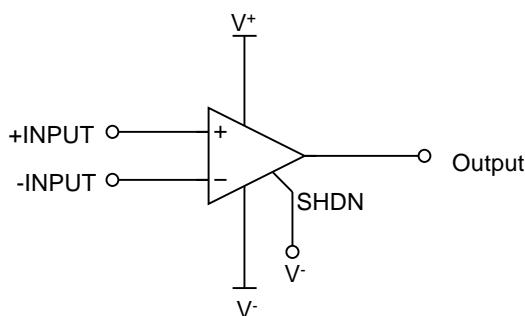
The NJU7098AF1-C has a shutdown pin. It can be disabled when the shutdown pin voltage is pulled at less than 0.5V above the negative supply, it can be enabled when the shutdown pin voltage is pulled at $V^+ - 0.5V$ or more above negative supply.

With the NJU7098AF1-C in shutdown mode, the output goes into high impedance mode. In this mode, the only path between the inputs and the output pin is through the external components around the device. So, for applications where there is active signal connection to the inverting input, with the NJU7098AF1-C in shutdown, the output could show signal swings due to current flow through these external components. For non-inverting amplifiers in shutdown, no output swings would occur, because of input-output isolation, with the exception of capacitive coupling.

In applications where shutdown operation is not needed and the NJU7098AF1-C is used, the shutdown pin should be open or connected to V^+ .



Normally Mode (Shutdown is disable)



Shutdown Mode (Shutdown is enable)

Single and Dual Supply Voltage Operation

The NJU7098AF1-C works with both single supply and dual supply when the voltage supplied is between V^+ and V^- . These amplifiers operate from single 3 to 10V supply and dual $\pm 1.5V$ to $\pm 5V$ supply.

Common-Mode Input Voltage Range

When the supply voltage does not meet the condition of electrical characteristics, the range of common-mode input voltage is as follows:

$$V_{ICM} (\text{typ.}) = V^- \text{ to } V^+ - 1.5V \quad (\text{Ta} = 25^\circ\text{C})$$

Difference of V_{ICM} when Temperature change, refer to typical characteristic graph. During designing, consider variations in characteristics for use with allowance.

Maximum Output Voltage Range

When the supply voltage does not meet the condition of electrical characteristics, the range of the typ. value of the maximum output voltage is as follows:

$$V_{OM} (\text{typ.}) = V^- + 5mV \text{ to } V^+ - 20mV \quad (R_L = 10k\Omega \text{ to } V, \text{ Ta} = 25^\circ\text{C})$$

During designing, consider variations in characteristics and temperature characteristics for use with allowance. In addition, also note that the output voltage range becomes narrow as shown in typical characteristics graph when an output current increases.

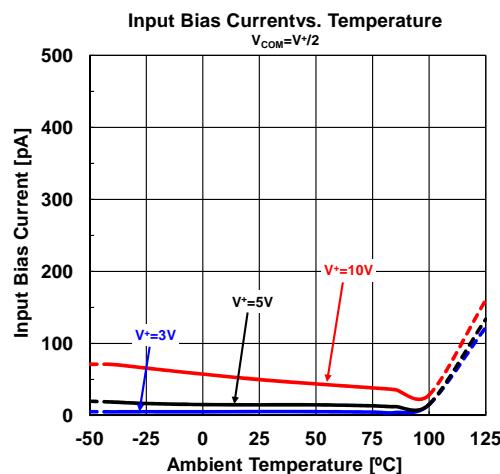
Thermoelectric Effect

The NJU7098AF1-C has a low offset voltage($15\mu\text{V}$) and zero-drift($0.05\mu\text{V}/^\circ\text{C}$) characteristics. Achieve a high performance, take care about thermoelectric effect possibly occurs on each input terminal. Generally, if there are thermal mismatches at the junction of different types of metals, the thermoelectric voltage (Seebeck effect) occurs at the junction. This voltage difference causes offset voltage and offset voltage drift. To minimize this voltage difference, the thermal mismatch in-between each input terminal and PCB metal should be minimized.

Input Bias Current

The NJU7098AF1-C has MOS input stage, and has very low bias current is 20pA at $V^+ = 5\text{V}$, $\text{Ta} = 25^\circ\text{C}$. But, as device temperature rises above approximately 100°C , the reverse leakage current of the input protection diodes becomes increasing, and input bias current rises rapidly with temperature(bias currents approximately double per 10°C increase).

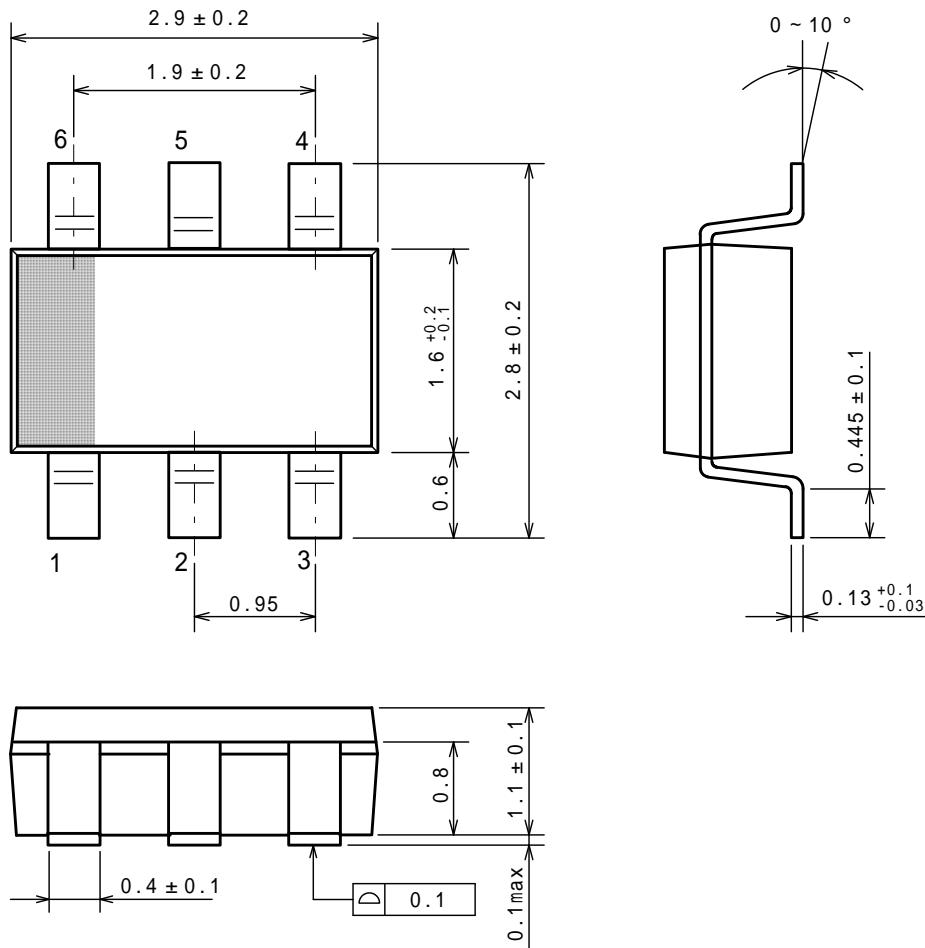
For detail of bias current with temperature, see typical characteristics "Input bias current vs. temperature".



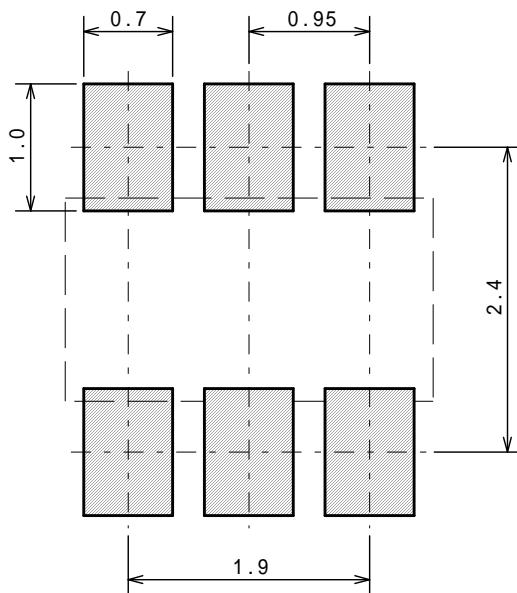
SOT-23-6-1

Unit: mm

■ PACKAGE DIMENSIONS

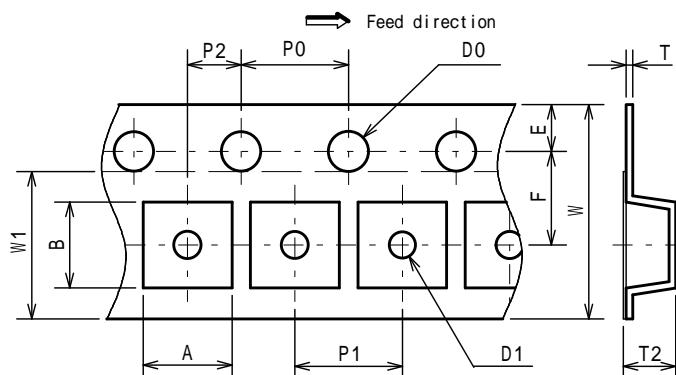


■ EXAMPLE OF SOLDER PADS DIMENSIONS

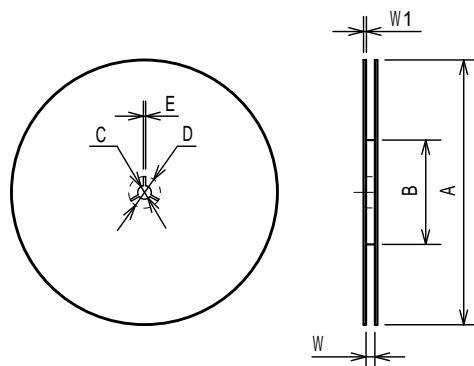


SOT-23-6-1**■ PACKING SPEC**

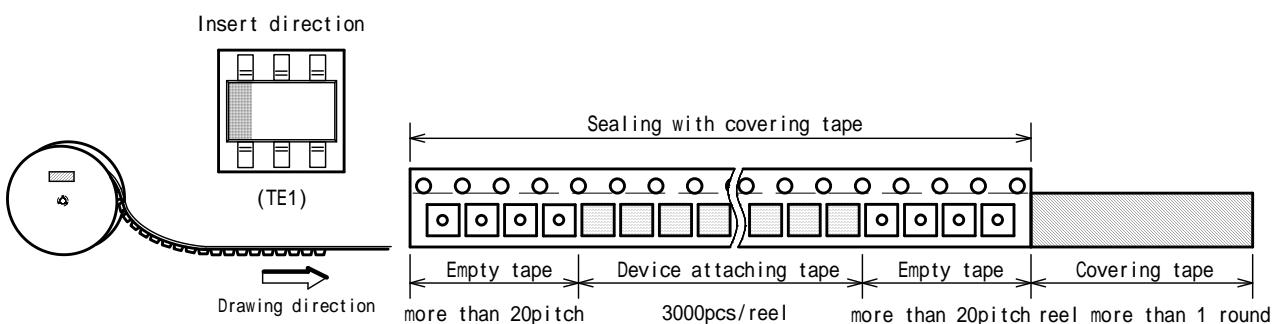
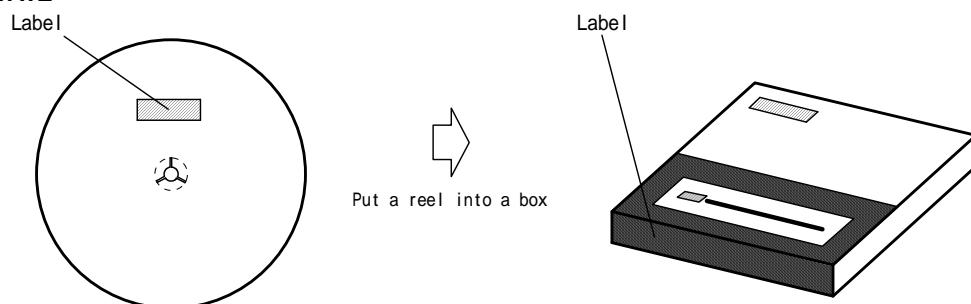
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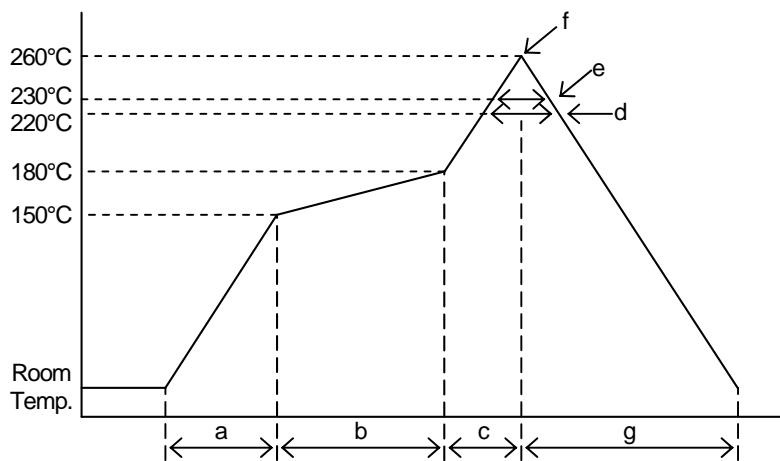
TAPING DIMENSIONS

SYMBOL	DIMENSION	REMARKS
A	3.3 ± 0.1	BOTTOM DIMENSION
B	3.2 ± 0.1	BOTTOM DIMENSION
D0	1.55	
D1	1.05	
E	1.75 ± 0.1	
F	3.5 ± 0.05	
P0	4.0 ± 0.1	
P1	4.0 ± 0.1	
P2	2.0 ± 0.05	
T	0.25 ± 0.05	
T2	1.5	
W	8.0 ± 0.3	
W1	5.5	THICKNESS 0.1MAX

REEL DIMENSIONS

SYMBOL	DIMENSION
A	180 ± 1
B	60 ± 1
C	13 ± 0.2
D	21 ± 0.8
E	2 ± 0.5
W	9 ± 0.5
W1	1.2 ± 0.2

TAPING STATE**PACKING STATE**

■ RECOMMENDED MOUNTING METHOD**INFRARED REFLOW SOLDERING PROFILE**

a	Temperature ramping rate	1 to 4°C/s
b	Pre-heating temperature Pre-heating time	150 to 180°C 60 to 120s
c	Temperature ramp rate	1 to 4°C/s
d	220°C or higher time	shorter than 60s
e	230°C or higher time	shorter than 40s
f	Peak temperature	lower than 260°C
g	Temperature ramping rate	1 to 6°C/s

The temperature indicates at the surface of mold package.

[CAUTION]

1. NJR strives to produce reliable and high quality semiconductors. NJR's semiconductors are intended for specific applications and require proper maintenance and handling. To enhance the performance and service of NJR's semiconductors, the devices, machinery or equipment into which they are integrated should undergo preventative maintenance and inspection at regularly scheduled intervals. Failure to properly maintain equipment and machinery incorporating these products can result in catastrophic system failures
2. The specifications on this datasheet are only given for information without any guarantee as regards either mistakes or omissions. The application circuits in this datasheet are described only to show representative usages of the product and not intended for the guarantee or permission of any right including the industrial property rights.
All other trademarks mentioned herein are the property of their respective companies.
3. To ensure the highest levels of reliability, NJR products must always be properly handled.
The introduction of external contaminants (e.g. dust, oil or cosmetics) can result in failures of semiconductor products.
4. NJR offers a variety of semiconductor products intended for particular applications. It is important that you select the proper component for your intended application. You may contact NJR's Sale's Office if you are uncertain about the products listed in this datasheet.
5. Special care is required in designing devices, machinery or equipment which demand high levels of reliability. This is particularly important when designing critical components or systems whose failure can foreseeably result in situations that could adversely affect health or safety. In designing such critical devices, equipment or machinery, careful consideration should be given to amongst other things, their safety design, fail-safe design, back-up and redundancy systems, and diffusion design.
6. The products listed in this datasheet may not be appropriate for use in certain equipment where reliability is critical or where the products may be subjected to extreme conditions. You should consult our sales office before using the products in any of the following types of equipment.
 - Aerospace Equipment
 - Equipment Used in the Deep Sea
 - Power Generator Control Equipment (Nuclear, steam, hydraulic, etc.)
 - Life Maintenance Medical Equipment
 - Fire Alarms / Intruder Detectors
 - Vehicle Control Equipment (Airplane, railroad, ship, etc.)
 - Various Safety Devices
7. NJR's products have been designed and tested to function within controlled environmental conditions. Do not use products under conditions that deviate from methods or applications specified in this datasheet. Failure to employ the products in the proper applications can lead to deterioration, destruction or failure of the products. NJR shall not be responsible for any bodily injury, fires or accident, property damage or any consequential damages resulting from misuse or misapplication of the products. The products are sold without warranty of any kind, either express or implied, including but not limited to any implied warranty of merchantability or fitness for a particular purpose.
8. Warning for handling Gallium and Arsenic (GaAs) Products (Applying to GaAs MMIC, Photo Reflector). These products use Gallium (Ga) and Arsenic (As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed of, please follow the related regulation and do not mix this with general industrial waste or household waste.
9. The product specifications and descriptions listed in this datasheet are subject to change at any time, without notice.

